DIODES

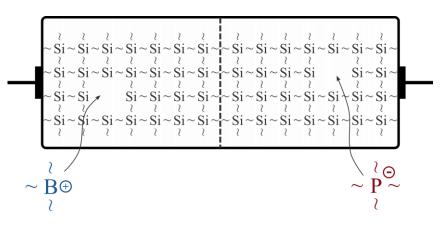
- What is a p-n junction?
- How p-n junction/diode operates?
- How do we address and use diodes in circuits?
- Types of diodes.

Diodes - p-n junction

How is the p-n junction created?

Silicon wafer (substrate, slice)

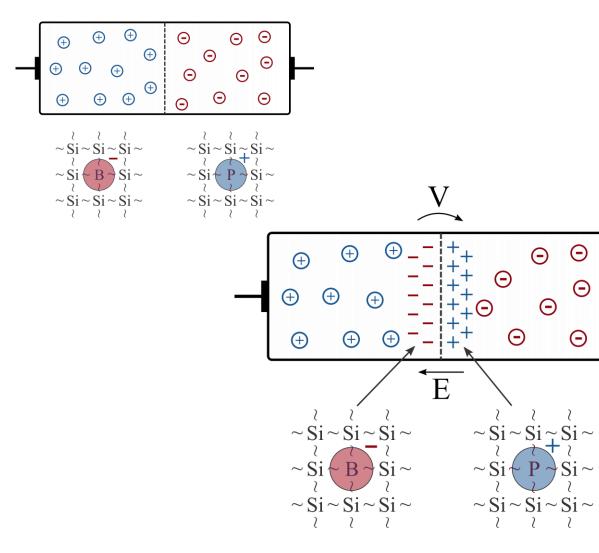
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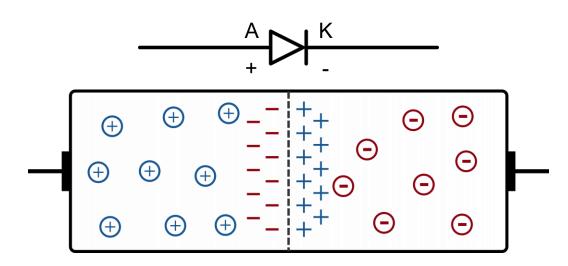


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Diodes - p-n junction

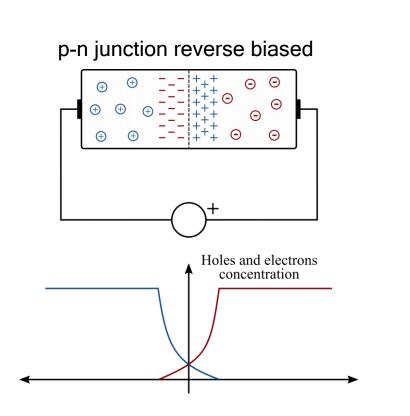
How is the p-n junction created?





P-type junction *p*⁺ majority charge *e*⁻ minority charge N-type junction p^+ minority charge *e* majority charge

Diodes - p-n junction polarization



p-n junction forward biased Θ Ð Θ (+)Θ (+)Θ Θ Ð \oplus Θ Ð Ð ΘΘ \oplus Θ Holes and electrons concentration Θ Ð Θ Ð Θ E Θ 0 Ð Θ \oplus Θ Θ

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$$p_c = p_{c0} \left(e^{kT\nu_d/q_e} - 1 \right)$$
$$\frac{dq(t)}{dt} = i(t) - \frac{q(t)}{\tau_L}$$
$$i(t) = \frac{q(t)}{\tau_L} = \frac{Q}{\tau_L} \left(e^{kT\nu_d(t)/q_e} - 1 \right)$$
$$= I_0 \left(e^{kT\nu_d(t)/q_e} - 1 \right)$$

k - Boltzmann's constant

T - temperature

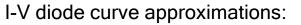
 q_e - the charge of the electron

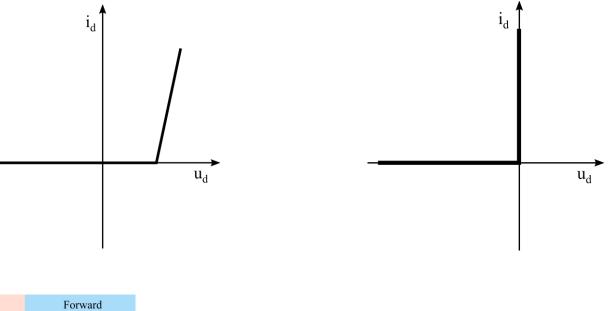
 τ_L - minority carriers (recombination) lifetime

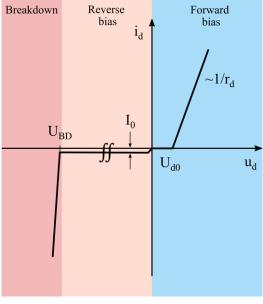
Diodes - I-V curve (static)

 i_d $-1/r_d$ U_{BD} $\int \int \int U_{d0}$ u_d

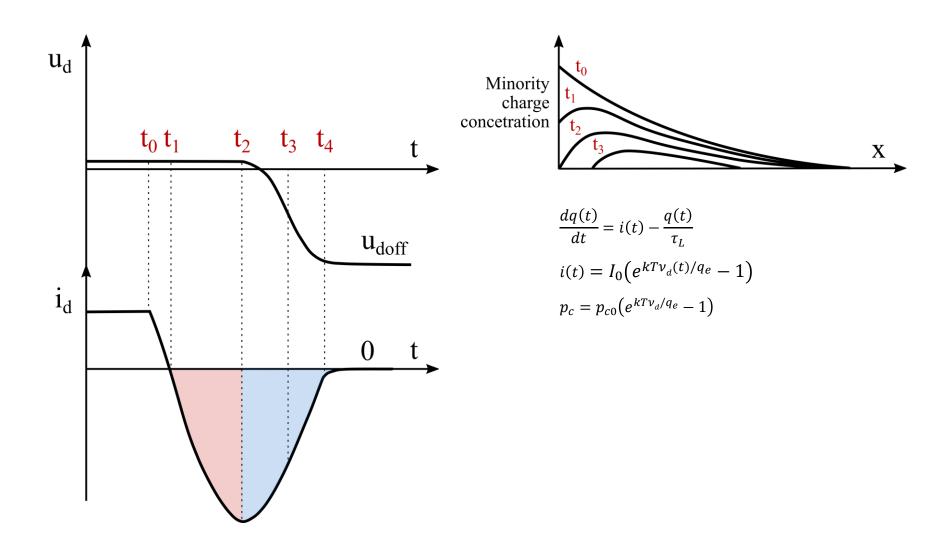
 $\begin{array}{l} u_{d} - \text{diode voltage} \\ i_{d} - \text{diode current} \\ U_{d0} - \text{diode turn-on voltage} \\ r_{d} - \text{diode internal resistance} \\ I_{0} - \text{diode leakage current} \\ U_{BD} - \text{diode breakdown voltage} \end{array}$







Diodes - Reverse recovery process

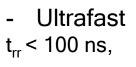


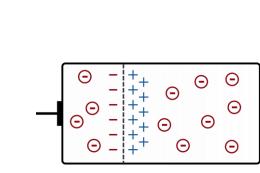
Diodes - types

Power diodes:



- Rectifying diodes $t_{rr} = n \cdot \mu s$
- Fast t_{rr} < μs, t_{rr} > 100 ns,





Light-emitting diodes



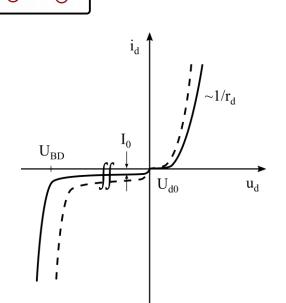


Zener diodes

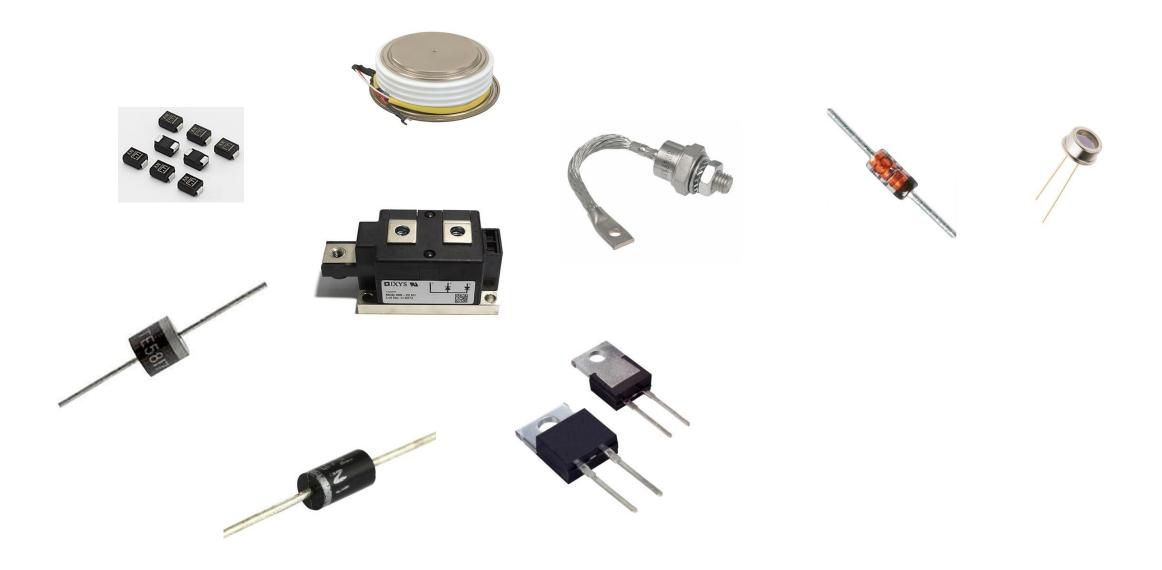
Photodiodes



- Schottky Unipolar (majority carrier) device Small(er) U_{do} (0.3 - 0.6 V), More efficient, Negligible reverse recovery process, Smaller U_{BD} , Higher I_0 .



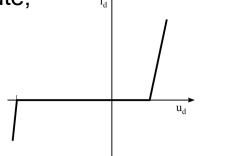
Diodes - packages



Diodes - important notes

Diodes are:

- Uncontrollable semiconductor devices,
- Turned ON and OFF by the circuit in which they are placed,
- Turned ON when the circuit imposes the "higher-thanzero" u_d *voltage*,
- Turned OFF when the circuit forces the diode *current* to fall to "zero",
- The first approximation is used for diode losses estimation in the ON state, i_a^{\dagger}



1_d

 \mathbf{u}_{d}

Diodes have complicated turn OFF process (reverse recovery process).